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INFORMATION DISCLOSURE STATEMENT

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Atty.Docket No.	Serial No.
0756-1363	08/~~479,211~~ 807737
Applicant	
Hisashi OHTANI et al.	
Filing Date	**Group**
06/07/95	[not yet assigned]

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
CR		5,147,826	09/15/92	Liu et al.	437	233	
CR		5,275,851	01/04/94	Fonash et al.	437	233	

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		Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	CR	C. Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon" (~~3 pages~~) Appl. PHYS Lett 60(1992)225
	CR	A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals", ~~Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR, pp. 635-640.~~ PHYS STAT SOL A95(1986)635
	CR	T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films", Solid State Communications, Vol. 85, No. 11, pp. 921-924, 1993.

Examiner L RADOMSKY — Date Considered 2/22/96

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Applicant
Hisashi OHTANI et al.

Filing Date
June 7, 1995

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Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)

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		Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No

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	LR	R. Kakkad et al., "Crystallized Si films by low-temperature rapid thermal annealing of amorphous silicon," J.Appl. Phys., 65(5), March 1, 1989, pp. 2069-72.
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